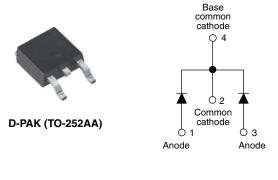
VS-MURD620CTPbF

Vishay Semiconductors

Ultrafast Rectifier, 2 x 3 A FRED Pt®



PRODUCT SUMMARY						
Package	D-PAK (TO-252AA)					
I _{F(AV)}	2 x 3 A					
V _R	200 V					
V _F at I _F	1.0 V					
t _{rr} typ.	See Recovery table					
T _J max.	175 °C					
Diode variation	Common cathode					

FEATURES

- Ultrafast recovery time
- Low forward voltage drop
- Low leakage current
- 175 °C operating junction temperature
- Compliant to RoHS Directive 2002/95/EC
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 $^\circ\mathrm{C}$

DESCRIPTION/APPLICATIONS

VS-MURD620CTPbF is the state of the art ultrafast recovery rectifier specifically designed with optimized performance of forward voltage drop and ultrafast recovery time.

The planar structure and the platinum doped life time control, guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in the output rectification stage of SMPS, UPS, DC/DC converters as well as freewheeling diode in low voltage inverters and chopper motor drives.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS							
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS			
Peak repetitive reverse voltage	V _{RRM}		200	V			
Average rectified forward current per device	I _{F(AV)}	Total device, rated V_R , $T_C = 146 \ ^\circ C$	6				
Non-repetitive peak surge current	I _{FSM}		50	А			
Peak repetitive forward current per diode	I _{FM}	Rated V _R , square wave, 20 kHz, T _C = 146 °C	6				
Operating junction and storage temperatures	T _J , T _{Stg}		- 65 to 175	°C			

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Breakdown voltage, blocking voltage	V _{BR} , V _R	I _R = 100 μA	200	-	-		
		I _F = 3 A	-	-	1.0		
Farmand welferer	V	I _F = 3 A, T _J = 125 °C	-	-	0.96	V	
Forward voltage V _F		I _F = 6 A	-	-	1.2		
		I _F = 6 A, T _J = 125 °C	-	-	1.13		
Deverse leekees eurrent		V _R = V _R rated	-	-	5		
Reverse leakage current I _R		$T_J = 125 \text{ °C}, V_R = V_R \text{ rated}$	-	-	250	μA	
Junction capacitance	CT	V _R = 200 V - 12 -		-	pF		
Series inductance	L _S	Measured lead to lead 5 mm from package body - 8.0 - n				nH	





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DYNAMIC RECOVERY CHARACTERISTICS ($T_J = 25$ °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CO	MIN.	TYP.	MAX.	UNITS		
		$I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}t =$	50 A/µs, V _R = 30 V	-	-	35		
Reverse recovery time t _{rr}		$I_F = 0.5 \text{ A}, I_R = 1.0$	-	-	25	20		
	۲r	$T_J = 25 \ ^\circ C$		-	19	-	ns	
		T _J = 125 °C			26	-		
Peak recovery current	1	T _J = 25 °C	I _F = 3 A dI _F /dt = 200 A/μs	-	3.1	-	А	
Peak recovery current I _{RRM}	IRRM	T _J = 125 °C	$V_{\rm R} = 160 \text{ V}$	-	4.6	-		
Reverse recovery charge	Q _{rr}	T _J = 25 °C		-	30	-	nC	
		T _J = 125 °C		_	60	-	no	

THERMAL - MECHANICAL SPECIFICATIONS							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Maximum junction and storage temperature range	T _J , T _{Stg}		- 65	-	175	°C	
Thermal resistance, junction to case per leg	R _{thJC}		-	-	9.0		
Thermal resistance, junction to ambient per leg	R _{thJA}		-	-	80	°C/W	
Thermal resistance, case to heatsink	R _{thCS}	Mounting surface, flat, smooth and greased	-	-	-		
Weight			-	0.3	-	g	
weight			-	0.01	-	oz.	
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)	
Marking device		Case style D-PAK	MURD620CT				



100

10

1

0.1

0

0.2 0.4 0.6 0.8

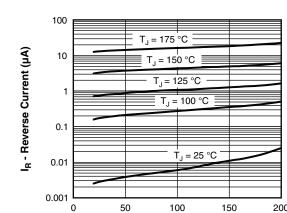
I_F - Instantaneous Forward Current (A)

VS-MURD620CTPbF

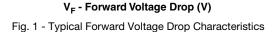
Ultrafast Rectifier, 2 x 3 A FRED Pt®

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200



0



= 175 °C T,

1.4

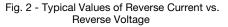
1.6

T_J = 150 °C

T_J = 25 °C

1.0 1.2

V_R - Reverse Voltage (V)



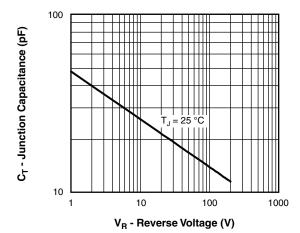


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

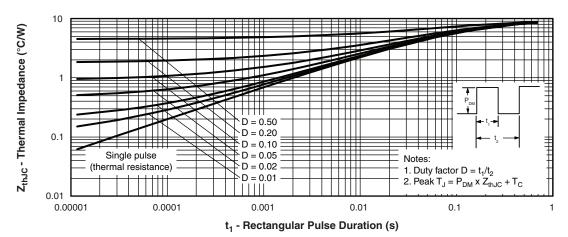


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

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Ultrafast Rectifier, 2 x 3 A FRED Pt[®]



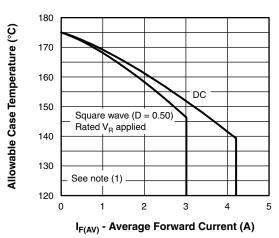


Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current

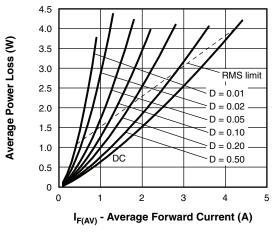


Fig. 6 - Forward Power Loss Characteristics

Note

 $^{(1)} \mbox{ Formula used: } T_C = T_J - (Pd + Pd_{REV}) \ x \ R_{th,JC}; \\ Pd = \mbox{ Forward power loss = } I_{F(AV)} \ x \ V_{FM} \ at \ (I_{F(AV)}/D) \ (see \ fig. \ 6); \\ Pd_{REV} = \ Inverse \ power \ loss = V_{R1} \ x \ I_R \ (1 - D); \ I_R \ at \ V_{R1} = \ Rated \ V_R$

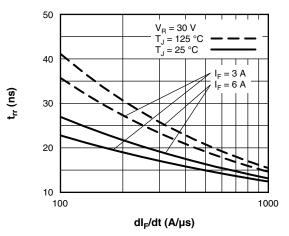


Fig. 7 - Typical Reverse Recovery Time vs. dI_F/dt

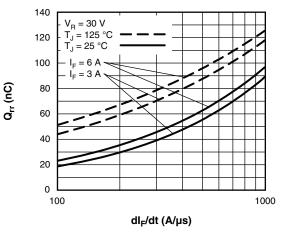


Fig. 8 - Typical Stored Charge vs. dl_F/dt



Ultrafast Rectifier, 2 x 3 A FRED Pt®

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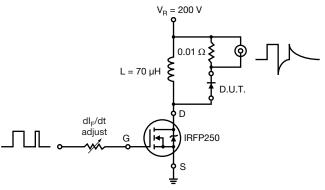
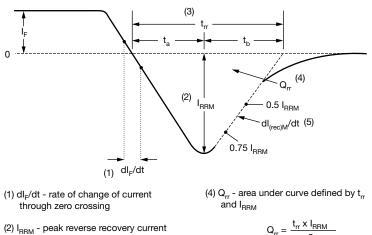


Fig. 9 - Reverse Recovery Parameter Test Circuit



$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

- (3) t_{rr} reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through 0.75 I_{RRM} and 0.50 I_{RRM} extrapolated to zero current.
- (5) dl_{(rec)M}/dt peak rate of change of current during t_b portion of t_{rr}
- Fig. 10 Reverse Recovery Waveform and Definitions

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PbF										SHAY
tors										
ON TAB	LE									
VS-	MUR	D	6	20	СТ	TRL	PbF			
5 -	Ultra D = Curr Volta CT = Tap	afast MI D-PAK rent rati age rati = Cente e and re	JR serie ng (6 = 0 ng (20 = r tap (du eel suffix	es 6 A) = 200 V) ual) <		TRL = 1	lape an	d reel (left ori		
	tors VS - 1 2 3 4 5 6 7 -	tors N TABLE VS- MUR (1) (2) (1) (tors Ult 2 > DN TABLE VS- MUR D 1 2 3 1 2 3 1 2 3 1 2 3 1 2 3 1 2 3 1 2 3 1 2 3 1 2 3 1 2 3 1 2 3 1 2 3 1 2 3	tors Ultrafast $2 \times 3 \text{ A F}$ DN TABLE VS- MUR D 6 (1) (2) (3) (4) (1) (2) (2) (3) (4) (1) (2) (2) (3) (4) (1) (2) (2) (3) (4) (4	tors Ultrafast Rect $2 \times 3 \text{ A FRED}$ DN TABLE VS- MUR D 6 20 (1) (2) (3) (4) (5) (1) (4) (4) (4) (4) (4) (1) (4) (4) (4) (4) (4) (4) (4) (4) (4) (4	tors Ultrafast Rectifier, $2 \times 3 \text{ A FRED Pt}^{\mathbb{R}}$ DN TABLE VS- MUR D 6 20 CT 1 2 3 4 5 6 1 - Vishay Semiconductors product 2 - Ultrafast MUR series 3 - D = D-PAK 4 - Current rating (6 = 6 A) 5 - Voltage rating (20 = 200 V) 6 - CT = Center tap (dual) 7 - Tape and reel suffix	tors Ultrafast Rectifier, $2 \times 3 \text{ A FRED Pt}^{\mathbb{R}}$ DN TABLE VS- MUR D 6 20 CT TRL 1 2 3 4 5 6 7 1 - Vishay Semiconductors product 2 - Ultrafast MUR series 3 - D = D-PAK 4 - Current rating (6 = 6 A) 5 - Voltage rating (20 = 200 V) 6 - CT = Center tap (dual) 7 - Tape and reel suffix TR = Ta TRL = 1 TRR = 1	tors Ultrafast Rectifier, $2 \times 3 \text{ A FRED Pt}^{\mathbb{R}}$ DN TABLE VS- MUR D 6 20 CT TRL PbF 1 2 3 4 5 6 7 8 1 - Vishay Semiconductors product 2 - Ultrafast MUR series 3 - D = D-PAK 4 - Current rating (6 = 6 A) 5 - Voltage rating (20 = 200 V) 6 - CT = Center tap (dual) 7 - Tape and reel suffix TR = Tape and TRL = Tape and TRL = Tape and TRL = Tape and TRR = Tape an	Ultrafast Rectifier, $2 \times 3 \ A \ FRED \ Pt^{(R)}$ ON TABLEVS-MURD620CTTRLPbF123456781-Vishay Semiconductors product2-Ultrafast MUR series3-D = D-PAK4-Current rating (6 = 6 A)5-Voltage rating (20 = 200 V)6-CT = Center tap (dual)TR = Tape and reel TRL = Tape and reel (left original trace)7-Tape and reel suffixTR = Tape and reel (right original trace)	tors Ultrafast Rectifier, $2 \times 3 \text{ A FRED Pt}^{(8)}$ DN TABLE VS- MUR D 6 20 CT TRL PbF 1 2 3 4 5 6 7 8 1 Vishay Semiconductors product 2 Ultrafast MUR series 3 D = D-PAK 4 Current rating (6 = 6 A) 5 Voltage rating (20 = 200 V) 6 CT = Center tap (dual) 7 Tape and reel suffix TR = Tape and reel (left oriented) TR = Tape and reel (right oriented) TR = Tape and reel (right oriented) TR = Tape and reel (right oriented)

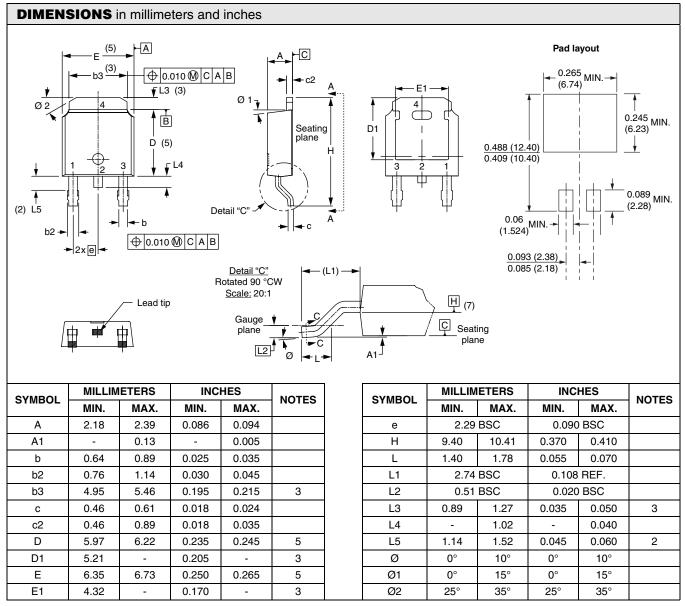
LINKS TO RELATED DOCUMENTS					
Dimensions	www.vishay.com/doc?95016				
Part marking information	www.vishay.com/doc?95059				
Packaging information	www.vishay.com/doc?95033				

ORDERIN



Vishay High Power Products

D-PAK (TO-252AA)



Notes

- $^{(1)}\,$ Dimensioning and tolerancing as per ASME Y14.5M-1994
- ⁽²⁾ Lead dimension uncontrolled in L5
- ⁽³⁾ Dimension D1, E1, L3 and b3 establish a minimum mounting surface for thermal pad
- (4) Section C C dimension apply to the flat section of the lead between 0.13 and 0.25 mm (0.005 and 0.10") from the lead tip
- ⁽⁵⁾ Dimension D, and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- ⁽⁶⁾ Dimension b1 and c1 applied to base metal only
- ⁽⁷⁾ Datum A and B to be determined at datum plane H
- ⁽⁸⁾ Outline conforms to JEDEC outline TO-252AA



Vishay

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